

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_C = +25^\circ C$
30V	12m Ω @ $V_{GS} = 10V$	37.8A
	16m Ω @ $V_{GS} = 4.5V$	32.8A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.


Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

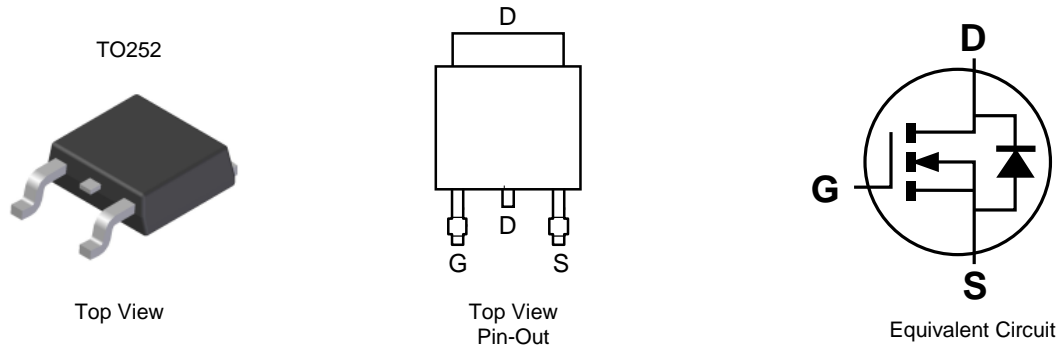
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)

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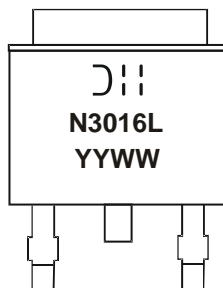


Ordering Information (Notes 4)

Product	Case	Packaging
DMN3016LK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



⏏ = Manufacturer's Marking
 N3016L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 14 = 2014)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	12.4 10	A
	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	I_D	37.8 30.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	17 13.6	A
Maximum Body Diode Continuous Current			I_S	2	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	90	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			I_{AS}	22	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			E_{AS}	24	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$		P_D	1.6	W
	$T_A = +70^\circ\text{C}$			1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	75	$^\circ\text{C/W}$
	$t < 10\text{s}$			34	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$		P_D	2.8	W
	$T_A = +70^\circ\text{C}$			1.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	46	$^\circ\text{C/W}$
	$t < 10\text{s}$			24	
Thermal Resistance, Junction to Case (Note 6)			$R_{\theta JC}$	3.1	
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.3	—	2.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8	12	mΩ	V _{GS} = 10V, I _D = 11A
		—	12	16		V _{GS} = 4.5V, I _D = 9A
Diode Forward Voltage	V _{SD}	—	0.70	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1415	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	119	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	82	—	pF	
Gate Resistance	R _G	—	2.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	25.1	—	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	11.3	—	nC	
Gate-Source Charge	Q _{gs}	—	3.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.6	—	nC	
Turn-On Delay Time	t _{D(on)}	—	4.8	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω,
Turn-On Rise Time	t _r	—	16.5	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	26.1	—	ns	
Turn-Off Fall Time	t _f	—	5.6	—	ns	
Body Diode Reverse Recovery Time	t _{rr}	—	12.3	—	ns	I _F = 12A, di/dt = 500A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	10.4	—	nC	

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- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. UIS in production with L = 0.1mH, starting T_A = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

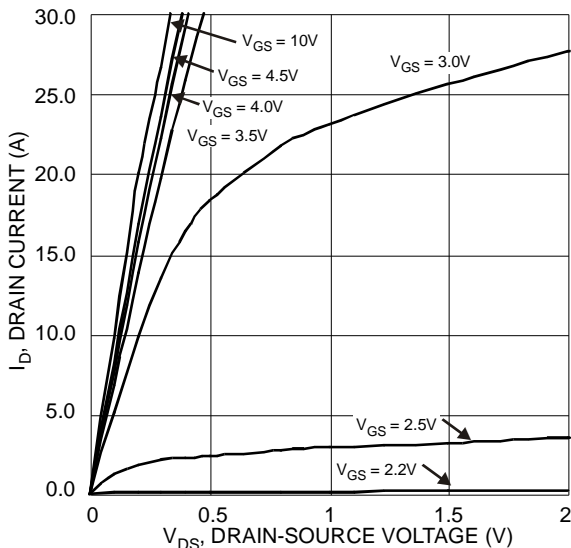


Figure 1 Typical Output Characteristic

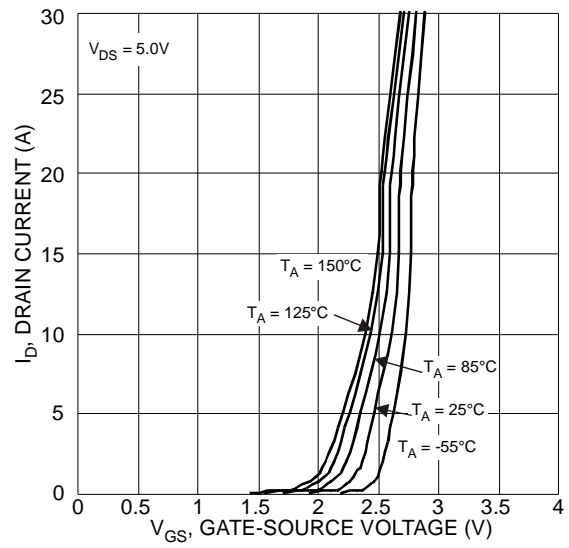


Figure 2 Typical Transfer Characteristics

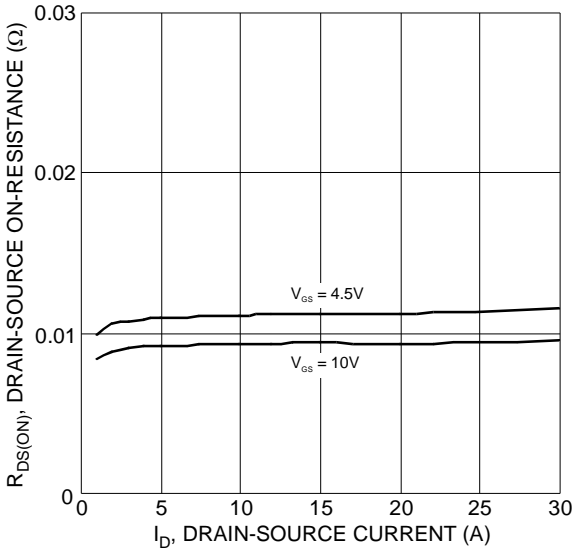


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

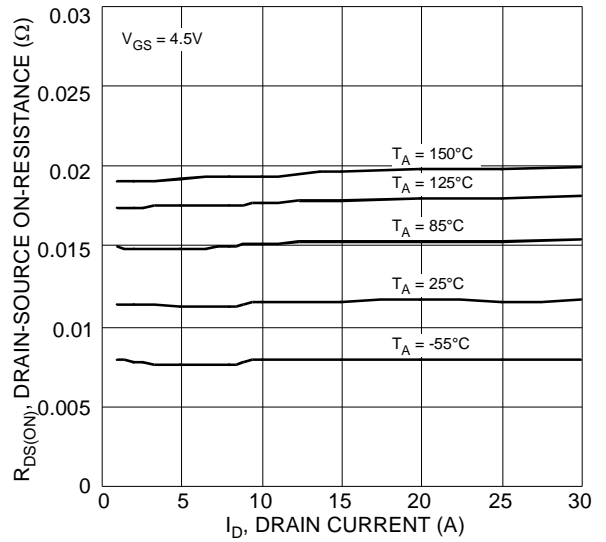


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

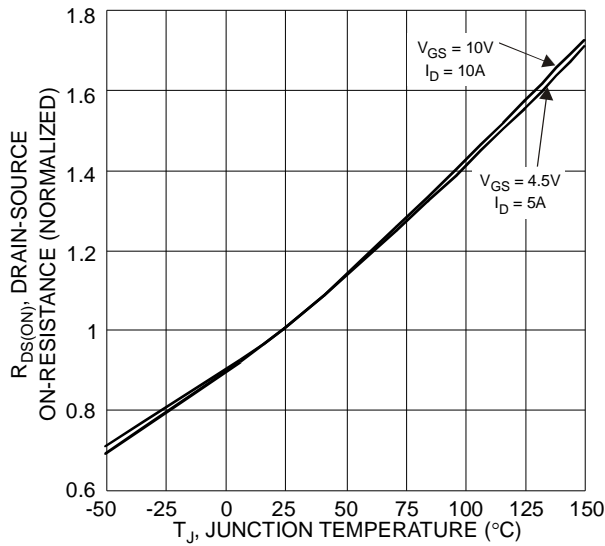


Figure 5 On-Resistance Variation with Temperature

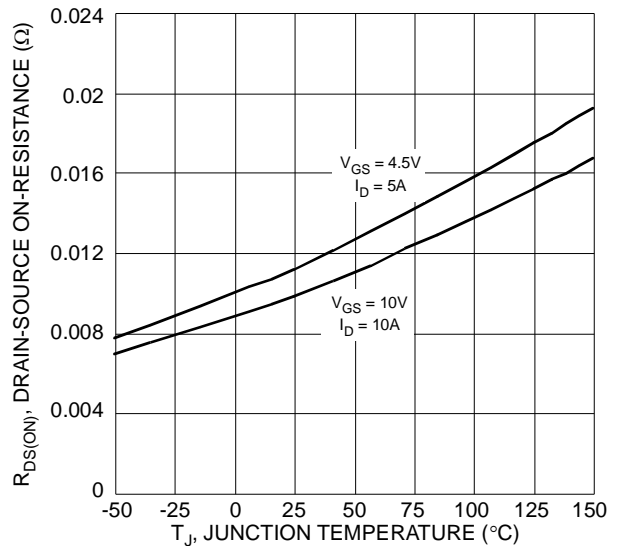


Figure 6 On-Resistance Variation with Temperature

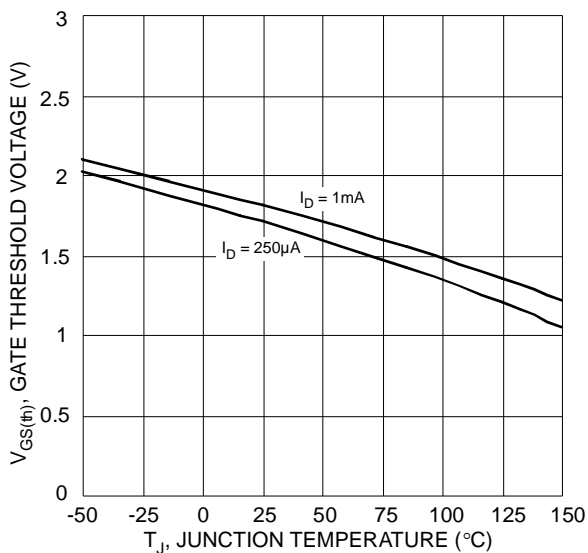


Figure 7 Gate Threshold Variation vs. Ambient Temperature

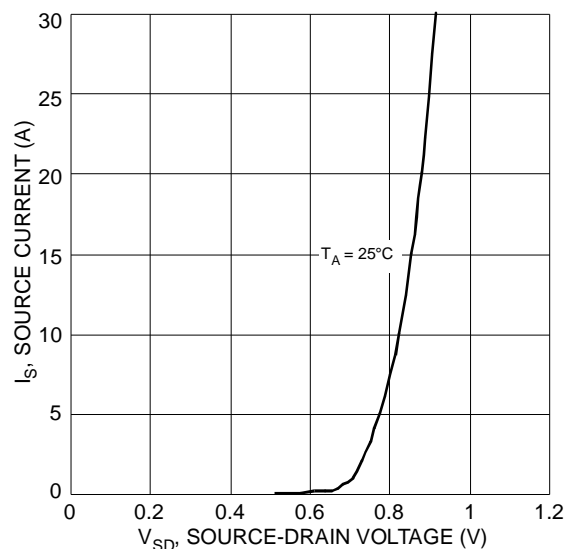


Figure 8 Diode Forward Voltage vs. Current

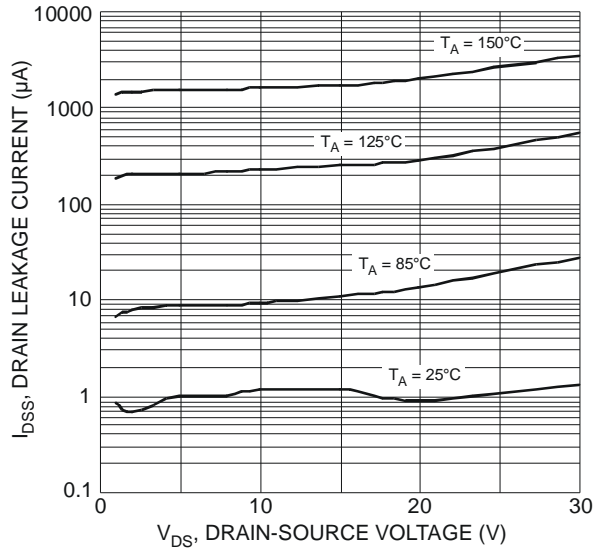


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

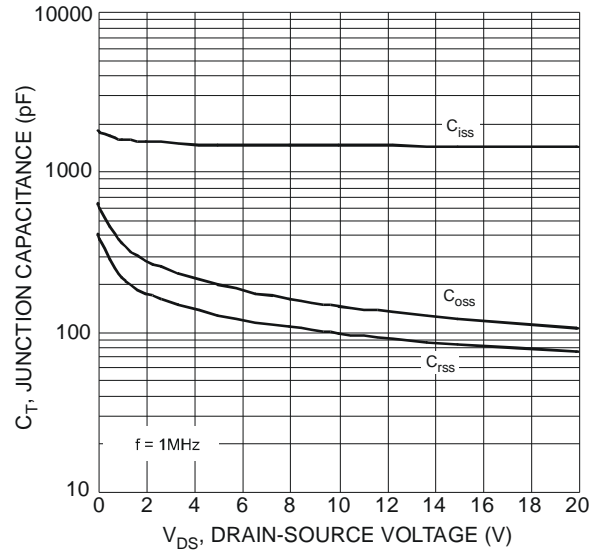


Figure 10 Typical Junction Capacitance

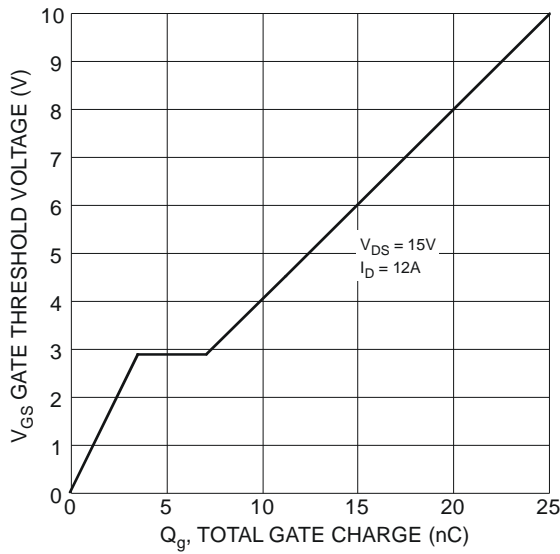


Figure 11 Gate Charge

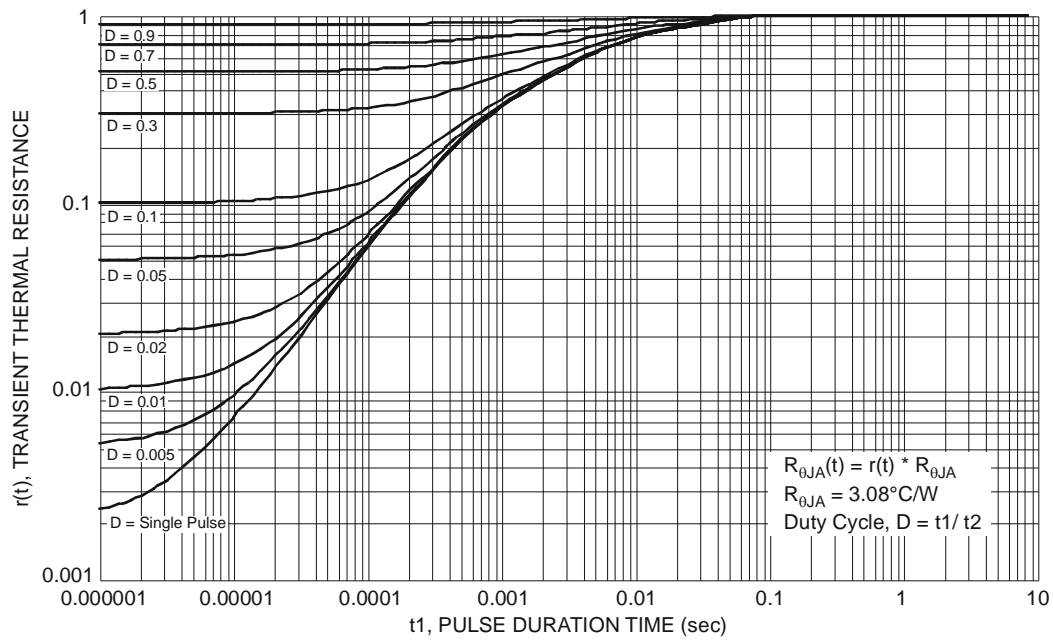
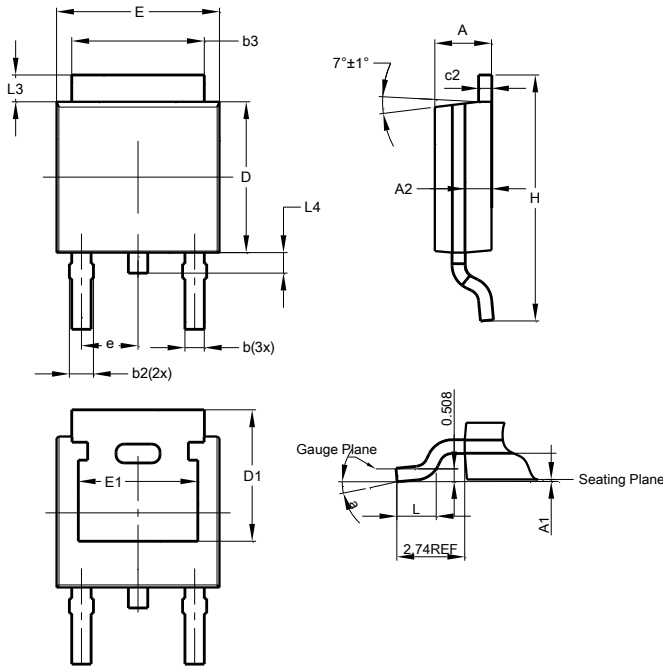


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

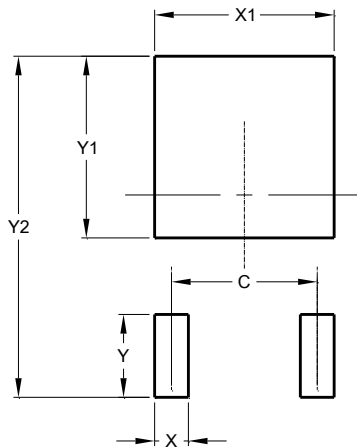


TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

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Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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